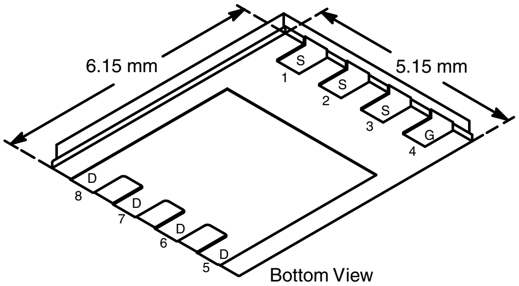
N-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω) Max.	I_D (A)[a]	Q_g (Typ.)
40	0.0027 at V_{GS} = 10 V	60	21.3 nC
	0.0040 at V_{GS} = 4.5 V	60	

PowerPAK® SO-8



Ordering Information:
SiR644DP-T1-GE3 (Lead (Pb)-free and Halogen-free)

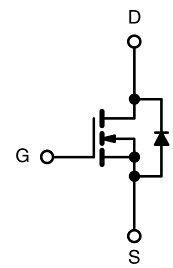
FEATURES

- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested
- Material categorization:
  For definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT
HALOGEN FREE

APPLICATIONS

- Synchronous Rectification
- DC/DC Converters
- DC/AC Inverters



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	40	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	60[a]	A
	T_C = 70 °C		60[a]	
	T_A = 25 °C		32.7[b, c]	
	T_A = 70 °C		26[b, c]	
Pulsed Drain Current (t = 100 µs)		I_{DM}	200	
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	60[a]	
	T_A = 25 °C		4.7[b, c]	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	35	
Single Pulse Avalanche Energy		E_{AS}	61	mJ
Maximum Power Dissipation	T_C = 25 °C	P_D	69	W
	T_C = 70 °C		44.4	
	T_A = 25 °C		5.2[b, c]	
	T_A = 70 °C		3.3[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature)[d, e]			260	

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[b, f]	t ≤ 10 s	R_{thJA}	19	24	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	1.2	1.8	

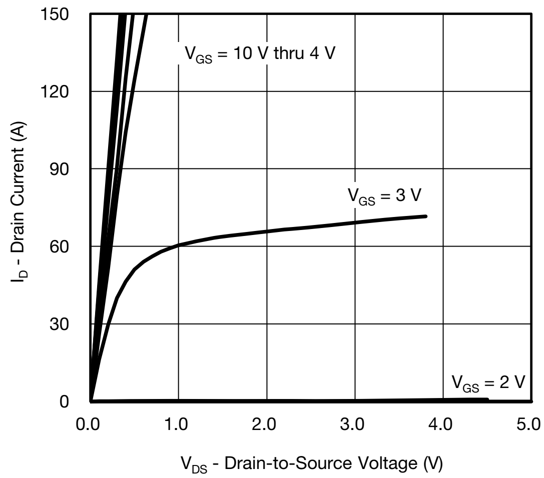
Notes:
a. Package limited.
b. Surface mounted on 1" x 1" FR4 board.
c. t = 10 s.
d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
f. Maximum under steady state conditions is 65 °C/W.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	40			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA		24		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 4.8		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 250 µA	1		2.2	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 40 V, V_{GS} = 0 V			1	µA
		V_{DS} = 40 V, V_{GS} = 0 V, T_J = 55 °C			10	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \geq$ 5 V, V_{GS} = 10 V	30			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 20 A		0.0022	0.0027	Ω
		V_{GS} = 4.5 V, I_D = 15 A		0.0030	0.0040	
Forward Transconductance[a]	g_{fs}	V_{DS} = 10 V, I_D = 20 A		87		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = 20 V, V_{GS} = 0 V, f = 1 MHz		3200		pF
Output Capacitance	C_{oss}			2460		
Reverse Transfer Capacitance	C_{rss}			160		
Total Gate Charge	Q_g	V_{DS} = 20 V, V_{GS} = 10 V, I_D = 20 A		47	71	nC
		V_{DS} = 20 V, V_{GS} = 4.5 V, I_D = 20 A		21.3	32	
Gate-Source Charge	Q_{gs}			7.5		
Gate-Drain Charge	Q_{gd}			12		
Output Charge	Q_{oss}	V_{DS} = 20 V, V_{GS} = 0 V		60	90	
Gate Resistance	R_g	f = 1 MHz	0.3	0.7	1.2	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 20 V, R_L = 1 Ω $I_D \cong$ 20 A, V_{GEN} = 10 V, R_g = 1 Ω		13	26	ns
Rise Time	t_r			5	10	
Turn-Off Delay Time	$t_{d(off)}$			29	55	
Fall Time	t_f			5	10	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 20 V, R_L = 1 Ω $I_D \cong$ 20 A, V_{GEN} = 7.5 V, R_g = 1 Ω		33	65	
Rise Time	t_r			120	240	
Turn-Off Delay Time	$t_{d(off)}$			33	66	
Fall Time	t_f			10	20	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C			60	A
Pulse Diode Forward Current (t_p = 100 µs)	I_{SM}				200	
Body Diode Voltage	V_{SD}	I_S = 5 A		0.74	1.1	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 10 A, dI/dt = 100 A/µs, T_J = 25 °C		54	105	ns
Body Diode Reverse Recovery Charge	Q_{rr}			59	120	nC
Reverse Recovery Fall Time	t_a			23		ns
Reverse Recovery Rise Time	t_b			31		

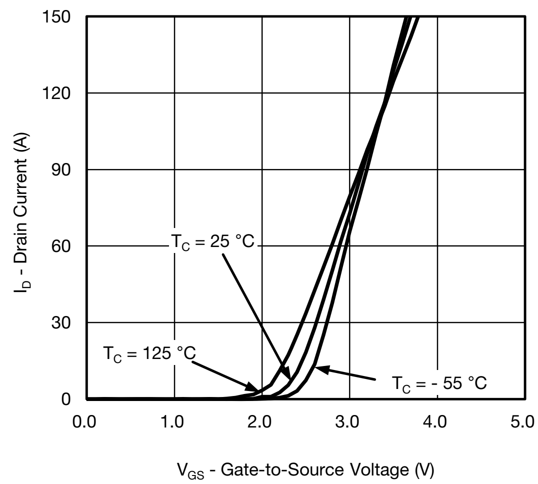
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

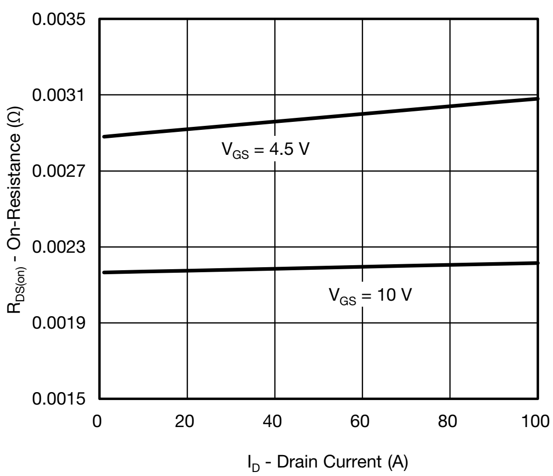
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



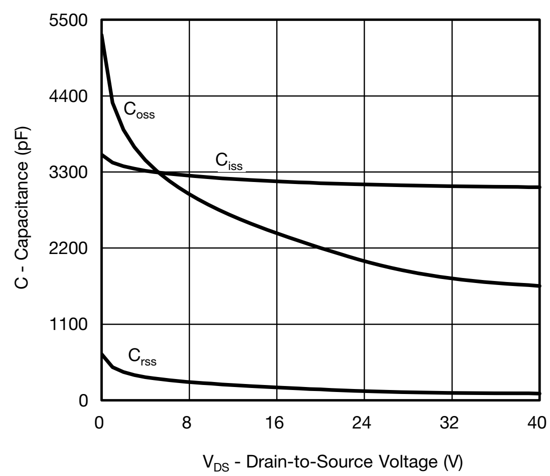
Output Characteristics



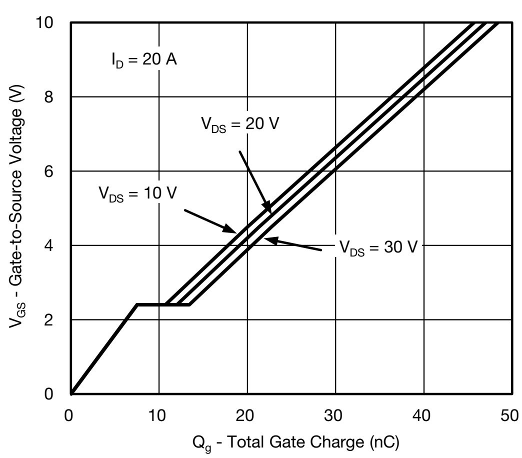
Transfer Characteristics



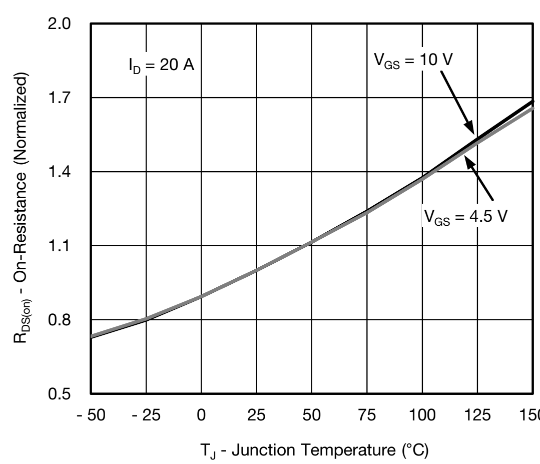
On-Resistance vs. Drain Current



Capacitance

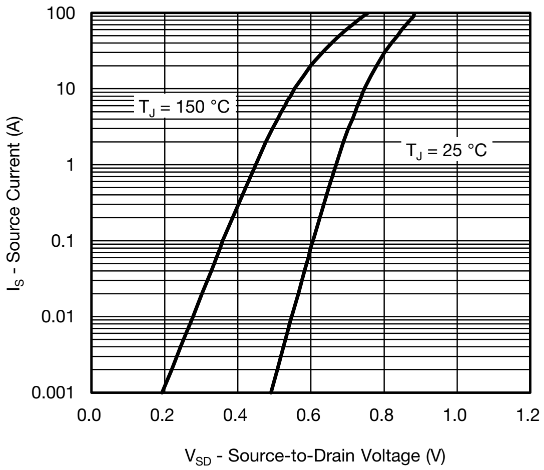


Gate Charge

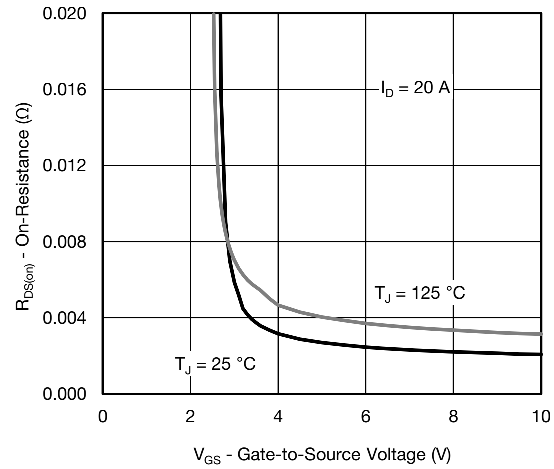


On-Resistance vs. Junction Temperature

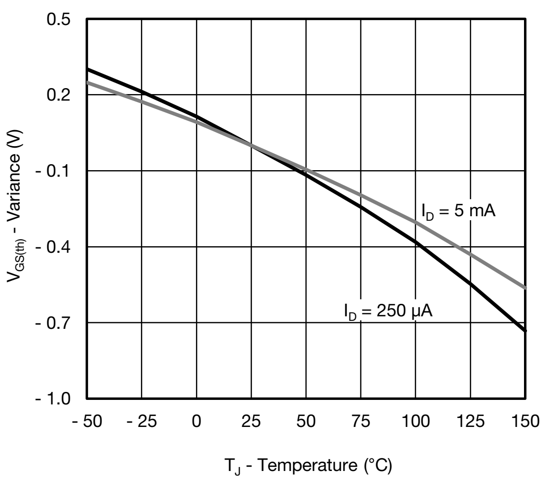
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



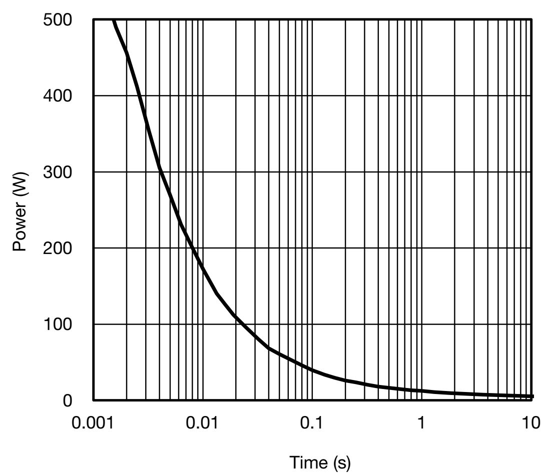
Source-Drain Diode Forward Voltage



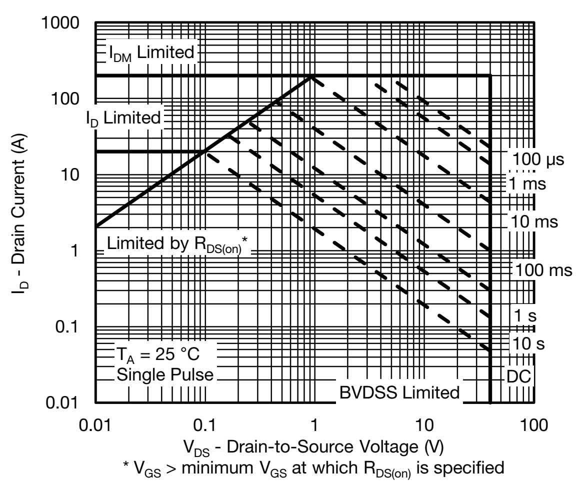
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

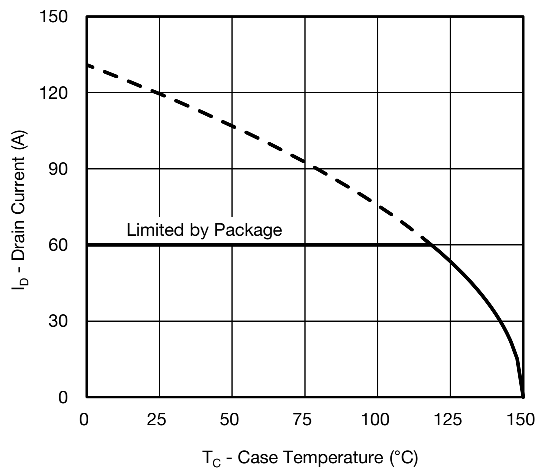


Single Pulse Power, Junction-to-Ambient

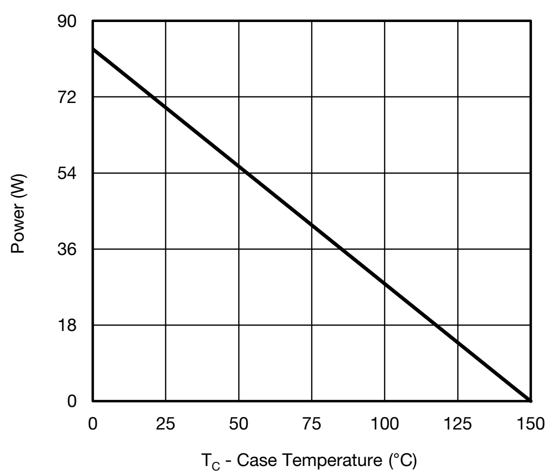


Safe Operating Area, Junction-to-Ambient

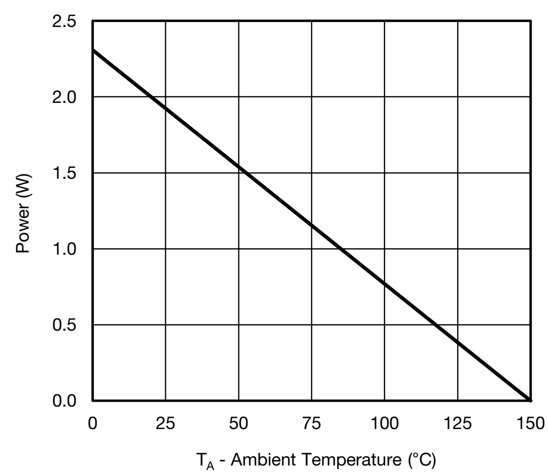
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



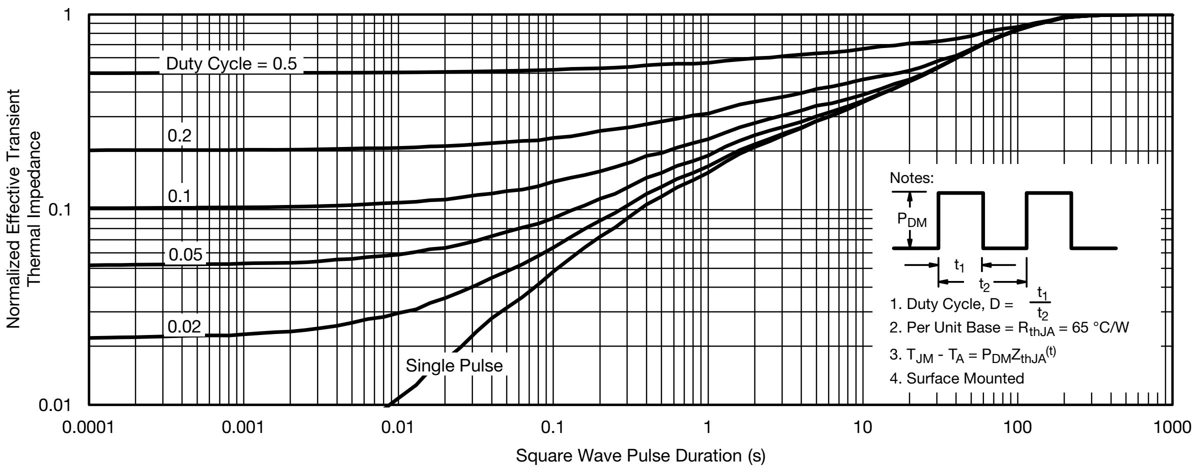
Power, Junction-to-Case



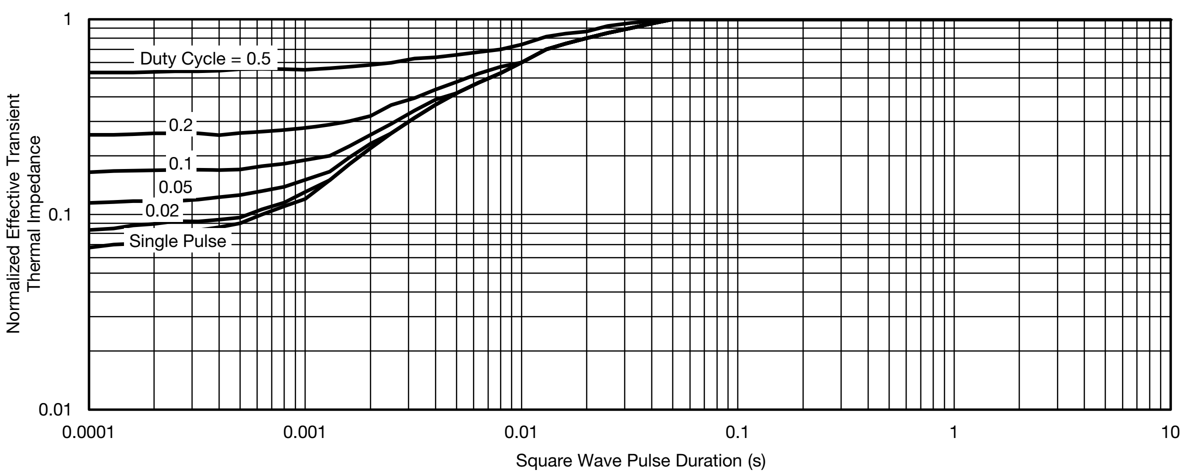
Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max.)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



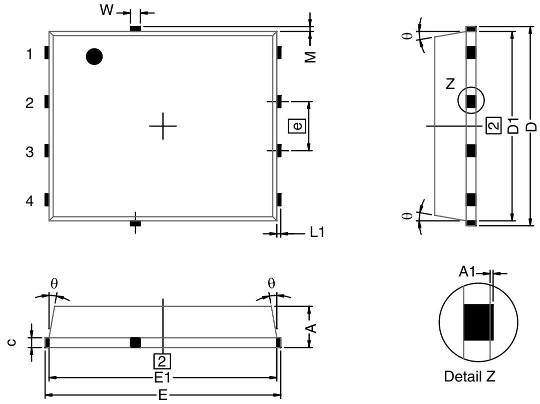
Normalized Thermal Transient Impedance, Junction-to-Ambient

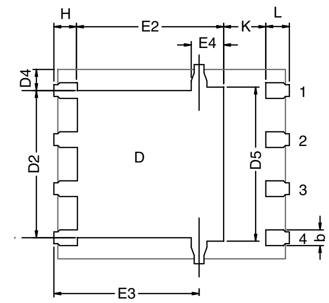


Normalized Thermal Transient Impedance, Junction-to-Case

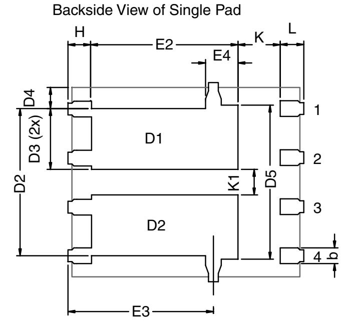
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62851.

PowerPAK® SO-8, (Single/Dual)





Backside View of Single Pad

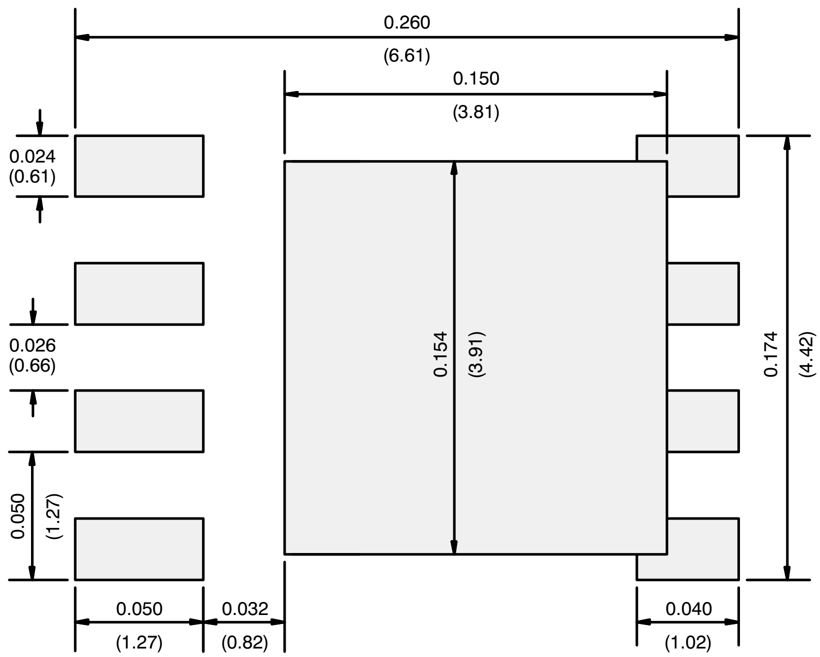


Backside View of Dual Pad

Notes
1. Inch will govern.
2 Dimensions exclusive of mold gate burrs.
3. Dimensions exclusive of mold flash and cutting burrs.

DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.97	1.04	1.12	0.038	0.041	0.044
A1		-	0.05	0	-	0.002
b	0.33	0.41	0.51	0.013	0.016	0.020
c	0.23	0.28	0.33	0.009	0.011	0.013
D	5.05	5.15	5.26	0.199	0.203	0.207
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.56	3.76	3.91	0.140	0.148	0.154
D3	1.32	1.50	1.68	0.052	0.059	0.066
D4		0.57 typ.			0.0225 typ.	
D5		3.98 typ.			0.157 typ.	
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	5.79	5.89	5.99	0.228	0.232	0.236
E2 (for AL product)	3.30	3.48	3.66	0.130	0.137	0.144
E2 (for other product)	3.48	3.66	3.84	0.137	0.144	0.151
E3	3.68	3.78	3.91	0.145	0.149	0.154
E4 (for AL product)		0.58 typ.			0.023 typ.	
E4 (for other product)		0.75 typ.			0.030 typ.	
e		1.27 BSC			0.050 BSC	
K (for AL product)		1.45 typ.			0.057 typ.	
K (for other product)		1.27 typ.			0.050 typ.	
K1	0.56	-	-	0.022	-	-
H	0.51	0.61	0.71	0.020	0.024	0.028
L	0.51	0.61	0.71	0.020	0.024	0.028
L1	0.06	0.13	0.20	0.002	0.005	0.008
θ	0°	-	12°	0°	-	12°
W	0.15	0.25	0.36	0.006	0.010	0.014
M		0.125 typ.			0.005 typ.	
ECN: C13-0702-Rev. K, 20-May-13 DWG: 5881						

RECOMMENDED MINIMUM PADS FOR PowerPAK® SO-8 Single



Recommended Minimum Pads
Dimensions in Inches/(mm)

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